

**Version With Markings To Show Changes Made**

**In the Claims:**

Please cancel Claims 15-26, 41-52, 54-57, 64-77, and 79-91.

Please amend Claim 53 as indicated below.

53.(Amended) A semiconductor memory device comprising:  
a semiconductor substrate;  
a lower electrode formed on the semiconductor substrate;  
a dielectric layer which is an oxide film including titanium and tantalum, on an upper surface of the lower electrode; and  
an upper electrode on an upper surface of the dielectric layer,  
wherein the density of titanium in the dielectric layer depends on the thickness of the dielectric layer;  
wherein the density of titanium of an area of the dielectric layer adjacent to the lower electrode is 0.1 to 15 percent.

Please amend Claim 63 as indicated below.

63.(Amended) A method for manufacturing a semiconductor memory device, the method comprising:  
(a) forming a lower electrode on an upper surface of a semiconductor substrate;  
(b) forming a dielectric layer of a oxide film including titanium and tantalum, on an upper surface of the lower electrode; and  
(c) forming an upper electrode on an upper surface of the dielectric layer,  
wherein, in step (b), the density of titanium in the dielectric layer depends on the thickness of the dielectric layer;  
wherein, in step (b), the density of titanium is adjusted to be 0.1 to 15 percent.

wherein the density of titanium of an area of the dielectric layer adjacent to the lower electrode is 0.1 to 15 percent.

Please amend Claim 63 as indicated below.

63.(Amended) A method for manufacturing a semiconductor memory device, the method comprising:

- (a) forming a lower electrode on an upper surface of a semiconductor substrate;
- (b) forming a dielectric layer of a oxide film including titanium and tantalum, on an upper surface of the lower electrode; and
- (c) forming an upper electrode on an upper surface of the dielectric layer,  
wherein, in step (b), the density of titanium in the dielectric layer depends on the thickness of the dielectric layer;  
wherein, in step (b), the density of titanium is adjusted to be 0.1 to 15 percent.